

UNISONIC TECHNOLOGIES CO., LTD

8550S

PNP SILICON TRANSISTOR

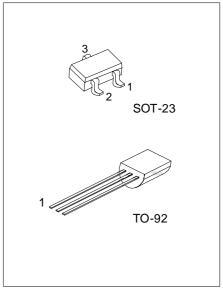
LOW VOLTAGE HIGH CURRENT **SMALL SIGNAL PNP TRANSISTOR**

■ FEATURES

*Collector current up to 700mA

*Collector-Emitter voltage up to 20 V

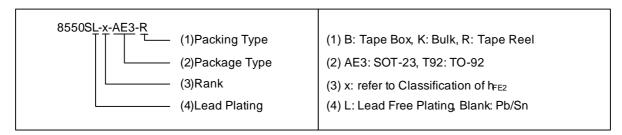
*Complimentary to 8550S



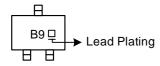
*Pb-free plating product number: 8550SL

ORDERING INFORMATION

Order Number		Dookogo	Pin Assignment			Dooking	
Normal	Lead Free Plating	Package	1	2	3	Packing	
8550S-x-AE3-R	8550SL-x-AE3-R	SOT-23	Е	В	С	Tape Reel	
8550S-x-T92-B	8550SL-x-T92-B	TO-92	Е	С	В	Tape Box	
8550S-x-T92-K	8550SL-x-T92-K	TO-92	E	С	В	Bulk	



MARKING (For SOT-23 Package)



■ ABSOLUTE MAXIMUM RATINGS (Ta = 25)

PARAMETER			RATING	UNITS
Collector-Base Voltage		V_{CBO}	-30	V
Collector-Emitter Voltage			-20	V
Emitter-Base Voltage			-5	V
Collector Dissipation/To 25	SOT-23	0	350	mW
Collector Dissipation(Ta=25)	TO-92	P _C	1	W
Collector Current		Ic	-700	mA
Junction Temperature		TJ	+150	°C
Storage Temperature	•	T _{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25 , unless otherwise specified)

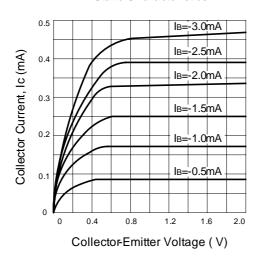
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_CBO	Ic=-100μA,I _E =0	-30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	Ic=-1mA,I _B =0	-20			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA,Ic=0	-5			V
Collector Cut-off Current	I _{CBO}	V_{CB} =-30 V , I_E =0			-1	uA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V,Ic=0			-100	nΑ
	h _{FE1}	V _{CE} =-1V,Ic=-1mA	100			
DC Current Gain	h _{FE2}	V _{CE} =-1V,Ic=-150 mA	120		400	
	h _{FE3}	V _{CE} =-1V,Ic=-500mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	Ic=-500mA,I _B =-50mA			-0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	Ic=-500mA,I _B =-50mA			-1.2	V
Base-Emitter Saturation Voltage	V_{BE}	V _{CE} =-1V,Ic=-10mA			-1.0	V
Current Gain Bandwidth Product	f⊤	V _{CE} =-10V,Ic=-50mA	100			MHz
Output Capacitance	Cob	V _{CB} =-10V,I _E =0, f=1MHz		9.0		pF

■ CLASSIFICATION OF h_{FE2}

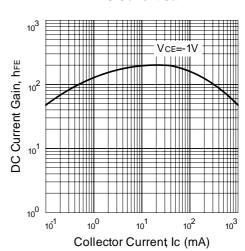
RANK	С	D	E
RANGE	120-200	160-300	280-400

TYPICAL CHARACTERISTICS

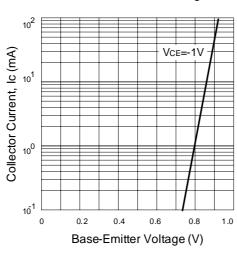




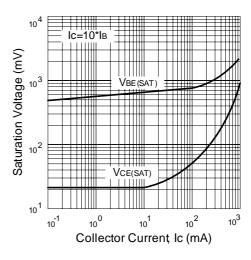
DC Current Gain



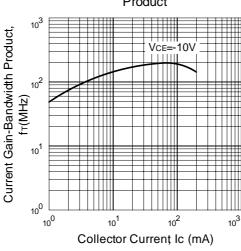
Base-Emitter on Voltage



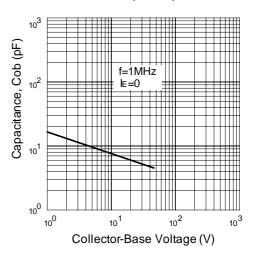
Saturation Voltage



Current Gain-Bandwidth Product



Collector Output Capacitance



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